

Analog Circuits
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Module - 03

Lecture – 05

And both V_T and $\mu_n C_{ox}$ vary with temperature. When knowing how much this varies, and how much V_T varies you can calculate the minimum and maximum quite easily. The range of g_m may be quite large. So, you what an amplifier gain ten, you could be get anywhere between five and twenty or something. So, we would like to keep a tighter control of gain or g_m . So, what we do, so for this let us examine the expression for the g_m ; I D I will use the simpler expression without channel length modulation or λ . So, this is $V_{GS} - V_T$ square times the current factor and g_m the expression we have been using is $\mu_n C_{ox} W$ by $L V_{GS} - V_T$.

Now, from this, we can write $V_{GS} - V_T$ as square root of 2 times I D. All I am doing is to solve for $V_{GS} - V_T$ here, just try it yourself by $\mu_n C_{ox} W$ by L . And if I substitute that in there, I will get another expression for g_m which is square root of 2 times $\mu_n C_{ox} W$ by L times I D. And finally, I can also write this as simply by examining this expression and this one yet another way of expressing $V_{GS} - V_T$ could be, all I did was the rearrange to the terms I have not written $V_{GS} - V_T$ in terms of I D alone $V_{GS} - V_T$ appears in both places, but this expression is correct it is just a rearrangement of this. And if I substitute that in here, this part will get cancelled out and I will get 2 times I D divided by $V_{GS} - V_T$. So, I have three different expressions for a g_m ; this one, that one and that one and all of them are correct of course, they are merely rearrangements of the same expression, but each one is useful in a different context.

If we hold V_{GS} fixed then clearly it make sense to use this there are no other hidden variables there is only one V_{GS} which is the operating point term in here and that is fixed. So, then you this it is very easy. So, if you know the current factor and the threshold voltage you can you can find out the g_m , now if by some means if for a given I D for a fixed value of I D we want to calculate the value of the g_m we can this one because I D is the only operating point term in this right there are no other operating point terms here and this one it is some time useful for making some calculations we will

see that later, but it has both I_D and V_{GS} now let us mainly look at this one and that one earlier we were using this.

But there is one special thing about this the second expression what is that, if I write it like this let me call this as current factor k_n . So, in this both g_m and V_T appear and if you look at this one only k_n appears this expression is independent of the threshold voltage, so now what does it mean for instance imagine the scenario we will later see how to come up with circuits that do this; the first one we already know how to fix the gate source voltage we can apply a voltage source between gate and source and in practice we use the resistive divider operating from a higher voltage and apply that voltage to the gate and source.

So, let us imagine a scenario where V_{GS} is fixed at three volts, remember what we are now trying to do is to find out the effect of variation of transistor characteristics. So, imagine that you have a test setup where you set the value of V_{GS} to be three volts and V_{DS} to be something. So, it is in saturation region and you can measure all kinds of things about the transistor. So, I set V_{GS} to be three volts and I can find the g_m of this I_D of this and of course, everywhere the assumption is that the transistor is in saturation. So, that is assumed. So, now we saw that as V_T changes in this case as V_T changes g_m will change, because V_{GS} fixed if V_T changes this will change and if current factor changes also the g_m will change.

So, if V_T change by some ΔV_T that is we originally had value of V_T and becomes V_T' difference is ΔV_T then g_m' would be $\mu_n C_{ox} W/L (V_{GS} - V_T - \Delta V_T)$ and g_m' divided by g_m would be remember just this part is the original g_m this is one minus ΔV_T divided by $V_{GS} - V_T$ because g_m originally was g_m was same expression without the ΔV_T , all and I am doing divide g_m' by original g_m and I get this relationship and similarly if K_n changes to K_n' what happens g_m' would be K_n' times $V_{GS} - V_T$ by the way.

I am assuming that in the first case only V_T has changed K_n does not change; and in the second case I am assuming that K_n has changed the current factor is changed and threshold voltage does not change, in practices, of course, both will change, but this is useful way calculate the effects separately. Then in this case g_m' divided by g_m

that is the new value of g_m compared to the original value of g_m is just K_n prime divided by K_n . So, this gives the relative change in g_m when V_T changes and you can see that operate the small $V_{GS} - V_T$, this effect will be even more for given ΔV_T . And here the ratio of changed g_m to the original g_m is simply the ratio of current factor, this is the scenario for fixed V_{GS} .

So, now, let me do something else; let me examine the scenario for the fixed current. I will explain exactly what I mean, later we will see how to get the what I mean in the case that I take my transistor, remember originally it had to have 3 volts the current of two hundred micro ampere and my method was just supply the 3 volts between gate and source, hope that the current 200 microampere g_m is 200 micro seimens. So, now, I try the alternative strategy when I buy a transistor, I do not know what is V_T etcetera. What I do is I apply some V_{GS} which is variable and I will have ammeter here and I will set the value of V_{GS} which will give a current of 200 micro amperes by the way I am not show the whole circuit here we cannot leave the drain open circuited an on so on.

It is assume that connected somewhere it is connected by voltage source, which is establishes V_{DS} and so on, so maybe I show it explicitly it sets the operating point V_{DS} . But in this case whatever transistor I have, I will go on varying V_{GS} until I come to two hundred micro ampere current and stop that; that means that I am operating with a fixed I_D . So, that is I_D is chosen that to be 200 micro amperes instead of choosing V_{GS} to be three volts. So, what happen in this case I know that the convenient expression use in this case square root of two times $\mu_n C_{ox} W$ by L times I_D . What happens if there is change in the threshold voltage that is the new value of V_T is the old value plus ΔV_T nothing because this expression does not have V_T at all. So, g_m prime will be the same as g_m , this is assuming that current has maintained at 200 micro amperes. And let us look at if K_n current factor changes to new current factor K_n prime you see that this expression for g_m has K_n inside the square root the ratio of the new g_m to the old g_m would be square root of K_n prime by K_n , so putting all the things together, we can see that if you fix the drain current I_D the variation in the g_m is lot smaller.

Let me put everything into a table, when I say fixed V_{GS} I mean that V_{GS} has been calculated for some nominal value of V_T and K_n that is I assume some value of V_T say 1 volt and some value of K_n say 100 microampere for per volt square, I know the g_m value that I want. So, I calculate V_{GS} . And in our example, it was three volts and for

that the current would be 100 micro amperes. Now, the problem we are facing is follows; when we buy many transistors or operate the same transistor at different temperatures I will not have V_T to be same and I will not have k_n to be the same. They will be all be different. The question is what to do in these situations; should I keep the gate source voltage fixed or should I somehow make the same current flow through the transistor.

Let us examine the scenario if you keep the fixed voltage something will happen, if we maintain the current to be fixed something else will happen. First let us look at what happen when the threshold voltage changes by ΔV_T , but K_n remains as it is. We already evaluated this, the ratio of new g_m to the old g_m is one minus ΔV_T by $V_{GS} - V_T$; and in this case, in case of fixed I_D , this is just one because V_T has no effect at all. Similarly, if I consider the change only in K_n , what happens, the ratio of new g_m to old g_m will be the ratio of current factors whereas in case of fixed I_D , it is the square root of the current factors. So, it is very easy to that g_m prime by g_m is much closer to one in this case. First of all, in case of V_T change there is no effect at all which is great, but in case of current factor change we have the square root let assume that K_n prime is 1.1, K_n that is current factor increase by 10 percent.

So, then in this case, this number will be 1.1 g_m also increases by ten percent whereas in this case this will be approximately 1.05. I assume you know this relationship for very small values of x square root of $1 + x$ is approximately one plus x by 2. So, square root of 1.1, which is square of $1 + 0.1$ is 1.05 approximately otherwise you can calculate using the calculator and see it will come out be close to this. So, although the current factor changes by ten percent g_m changes only by five percent in this case. So, this biasing fixing the values of V_{GS} , although that was kind of natural and that what we started with it is not a very good way of doing it, it does not very robust and g_m changes quite a lot with temperature and with different devices whereas in this it also changes, but by lot lesser amount. So, what we need to do now is to find out ways of biasing the transistor where the current will be fixed not the gate source voltage, we will see how to do that in forthcoming lessons.